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PCMI SPRING CONFERENCE 2025



Imaging of Liquid and Dry Film Photoresists – Best Practices From an Imaging Point of View

Presentation by: Dennis Pusch

Imaging of Liquid and Dry Film Photoresists – Best Practices From an Imaging Point of View

ABSTRACT

In modern microelectronics and PCM manufacturing, resist materials are critical to the lithography process used to create and form complex patterns on a substrate.

Two of the most common resist types are liquid resist and dry film resist, each offering specific advantages and disadvantages depending on the manufacturing process requirements.

While Liquid resist is a liquid form of photoresist applied to the surface of a substrate by spin coating, this technique enables a thin and uniform coating, making it particularly suitable for high-precision applications.

In contrast, dry-film resist is applied to the substrate in the form of solid films by a heat-depositing lamination process. This process may be mechanically more efficient and offers greater planarity over larger areas, suitable for applications where a uniform film thickness is required.

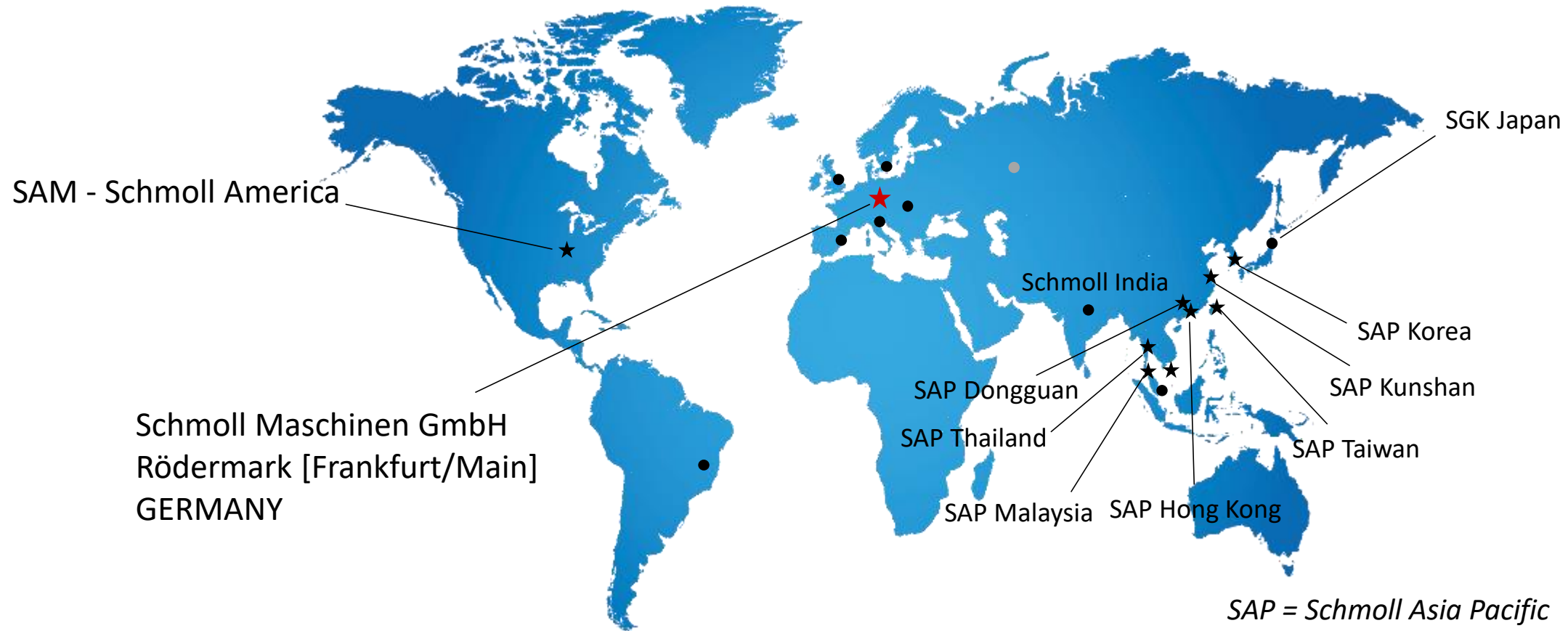
Since photolithography is considered a crucial technology for creating complex patterns and shapes in the chemical etching or PCM industry, this presentation will focus on a practical evaluation of working with both liquid and dry film resists using modern direct imaging technology.



- ▶ Business: Worldwide supplier for PCB/Substrate technology
- ▶ Segment: High Quality equipment for **M**echanical and **O**ptical PCB processing & related markets & applications
- ▶ Location: Rödermark/ Germany [near Frankfurt/Main]
- ▶ Employees: Germany over 350, worldwide more than 500
- ▶ Capacity: up to 100 Machines/month
- ▶ Installation: worldwide 16,500 units
- ▶ Founded: 1943 by Heinz Schmoll
- ▶ Company profile: Family business (President Mr. Thomas Kunz)
- ▶ PCMI Member: Since 2024

 Made
in
Germany





→ Market presence and **customer proximity**

Mechanical Micro Machining



Machines:

Drilling/Routing
Registration, Punch



Optical Micro Processing



Machines:

Laser Drilling & Cutting
Direct Imaging



Department: MDI

- Own production facility
- Own software department
- Team of technicians & engineers
- Total: **40** people dedicated to the **Direct Imaging** product line

Automated Line



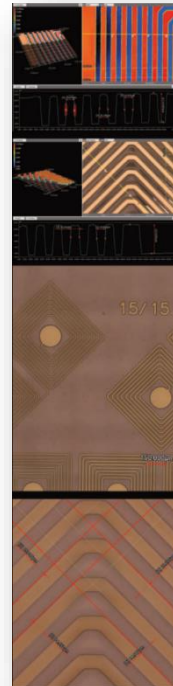
MDI-TTG & ROBOMATION

- ❖ Automatated In-Line system (<10 Sek. ·)
- ❖ Complete system solution DI & Automation from **single source**
- ❖ Can be integrated in line or as island solution possible
- ❖ [Conveyer to conveyer]
[loader to unloader]

Tandem Table Platform



MDI-TTG (Tandem Table)



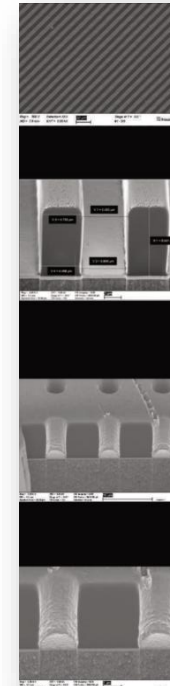
- ❖ Efficient Tandem-Table-Design, max. Panelformat **24"x36"** (per table)
- ❖ Optional Gantry-Mode for 54"x36"
- ❖ **Multi-Wavelengths-**system for all applications

24" = 610 mm
36" = 914 mm
54" = 1371 mm

Fineline Imaging (7µm L/S)



MDI-ST ULTRA



- ❖ Highest resolution & accuracy;
Ultra-Platform
- ❖ Resolutions of **7 µm L/S** (and smaller)
- ❖ Installation base and Application-Know-how

Reel-to-Reel

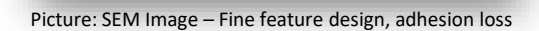


MDI-FLEX

- ❖ Reel-to-Reel Platform
- ❖ Vacuum solution for Flex-materials
- ❖ Autom. Winder & Unwinder

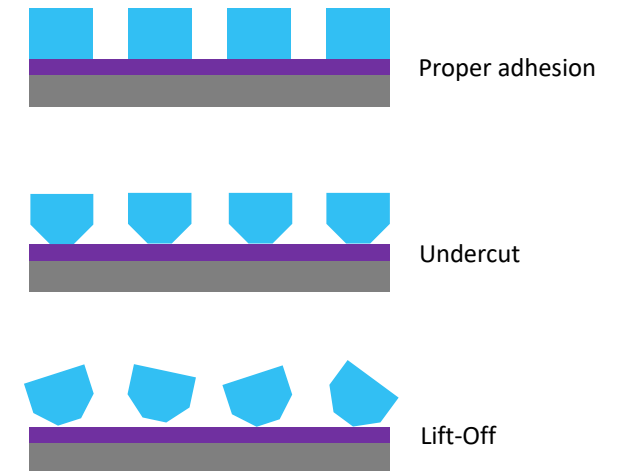


Challenge	Impact	Common Causes
Etch Uniformity	Inconsistent product quality	Poor bath control, resist variation
Etchant Management	Poor process control, waste	Degraded chemicals, oxidation loss
Undercutting	Dimensional inaccuracy	Isotropic etching, long etch times
Environmental Compliance	Legal/financial risk	Hazardous chemical disposal
Cost and Throughput	Higher operational costs	Low yields, inefficient processes
Resolution Limits	Feature size limitations	Mask quality, resist resolution
Photoresist Issues	Pattern defects, rework	Poor adhesion, contamination
Process Scaling	Inconsistent results in mass production	Equipment limits, parameter shifts



- **Challenge:** Achieving consistent etch depth and pattern accuracy across the entire surface.
- **Why it matters:** Uneven etching can cause dimensional errors, poor resolution and consequently product failure
- **Possible causes:**
 - **Variations in photoresist coating or exposure**
 - Uneven agitation or temperature in etching bath
 - Inconsistent chemical concentration or flow rate

- **Challenge:** Poor adhesion or defects in the photoresist can lead to pinholes, lift-off, or pattern loss during etching.
- **Possible solutions:**
 - Improved surface preparation and cleaning
 - **Optimized** soft bake and **exposure parameters**



IMAGING OF LIQUID AND DRY FILM PHOTORESIST

**1) Substrate Preparation**

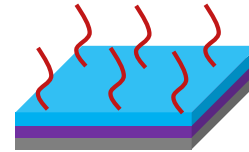
Goal / Purpose:

- Clean surface for resist application

**2) Photoresist Application**

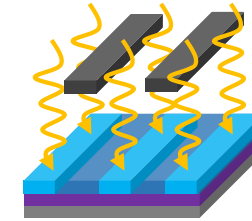
Goal / Purpose:

- Coat the surface with uniform photosensitive layer

**3) Soft Bake (Prebake)**

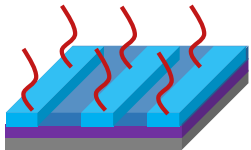
Goal / Purpose:

- Remove solvents,
- improve adhesion

**4) Exposure**

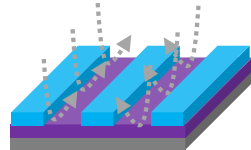
Goal / Purpose:

- Create pattern
- Change resist solubility through light exposure

**5) Post-Exposure Bake (Optional)**

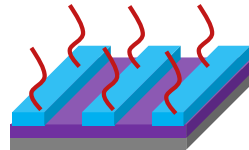
Goal / Purpose:

- Improve image stability

**6) Development**

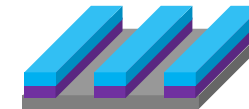
Goal / Purpose:

- Reveal pattern by dissolving resist
- Remove exposed (positive) or unexposed (negative) areas

**7) Hard Bake (Optional)**

Goal / Purpose:

- Strengthen resist to withstand etching chemicals

**8) Chemical Etching**

Goal / Purpose:

- Chemically remove exposed metal/material

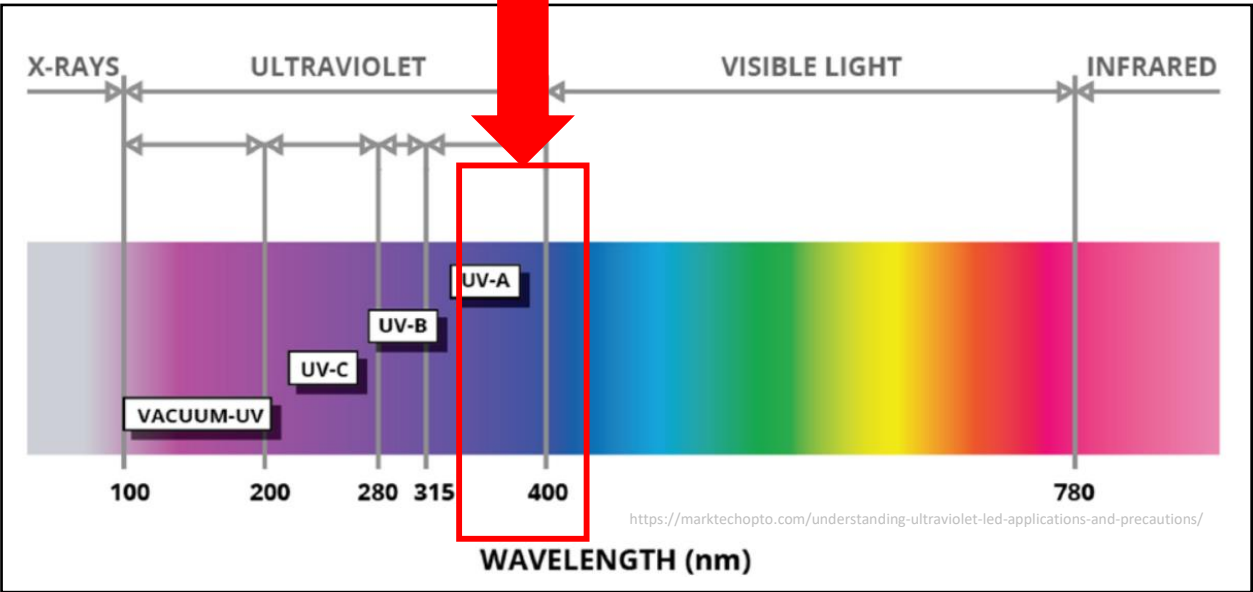
**9) Photoresist Stripping**

Goal / Purpose:

- Remove remaining photoresist

PCM

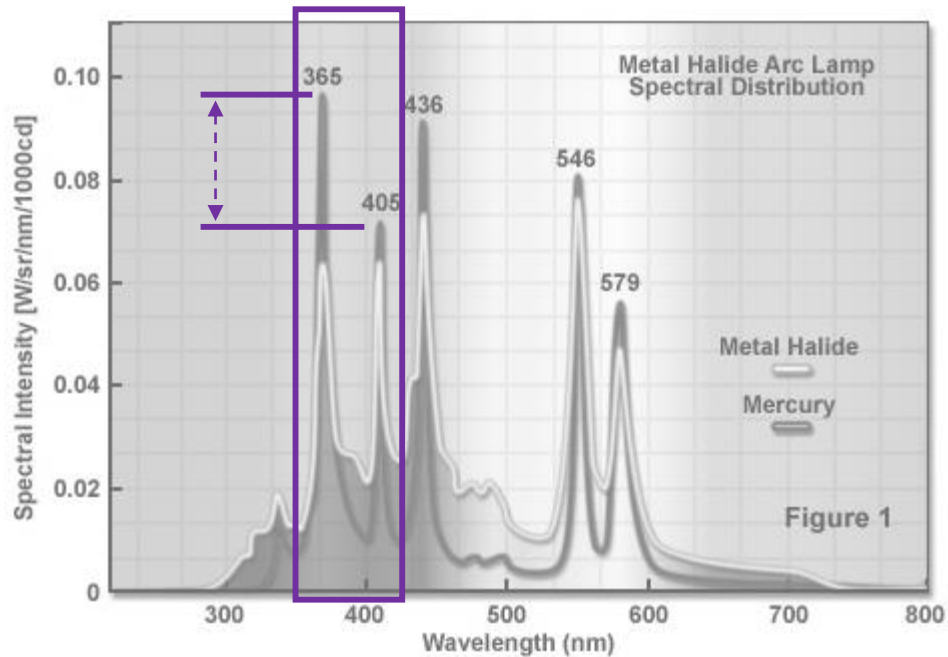
LIGHT SOURCE - UV SPECTRUM



The i-line in UV spectrum corresponds to a wavelength of 365 nm, while the h-line corresponds to a wavelength of 405 nm. Both are used in photolithography, a process that uses UV radiation to expose and pattern photoresists. I-line (365 nm) and h-line (405 nm) are also part of the broadband UV spectrum (350-450 nm) which includes the g-line at 436 nm.

- Elaboration:
- **i-line:** Represents a strong emission peak in the mercury spectrum at 365 nm.
 - **h-line:** Represents another strong emission peak in the mercury spectrum at 405 nm.
 - **Broadband UV:** This is a wider range of UV radiation, encompassing wavelengths including the i-line, h-line, and g-line (436 nm).
 - **Photolithography:** This process utilizes these UV wavelengths to expose and develop photoresists, which are light-sensitive materials used in the fabrication of microstructures like those found in semiconductor chips and other devices.
 - **UV-LED Sources:** In recent years, UV-LEDs have emerged as alternatives to traditional mercury lamps for UV exposure in photolithography.

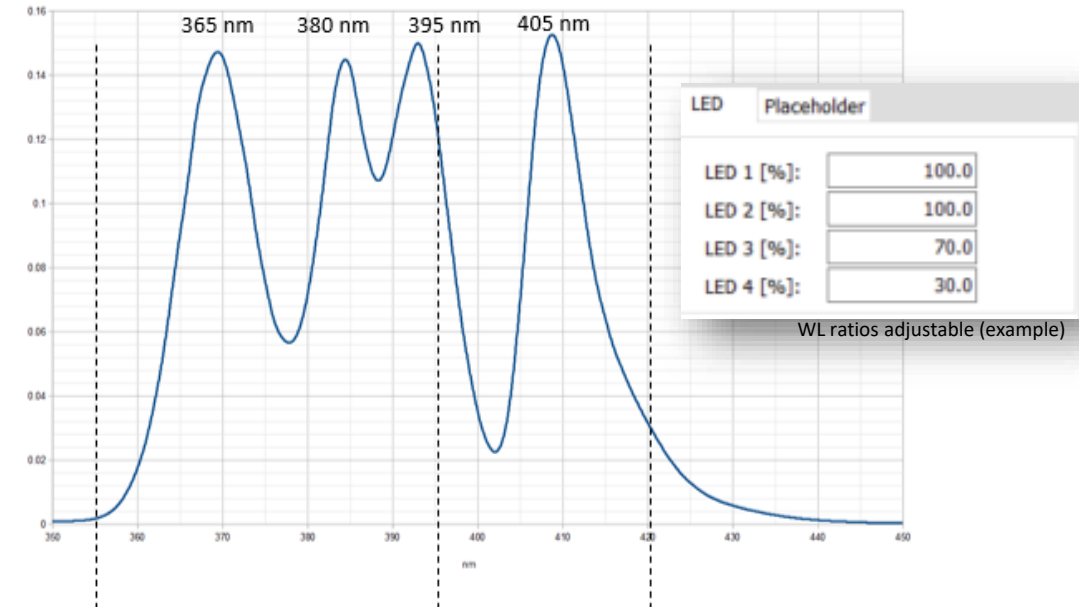
Aspect	Conventional Exposure (Lamp-based)	Direct Imaging (LED-based)
Light Source	UV lamp (e.g., mercury, metal halide)	High-intensity UV LEDs (often 365/385/405 nm)
Pattern Delivery	Uses photomasks to project patterns	Uses digital files to expose pattern directly
Exposure Mode	Full-field (entire mask area at once)	Pixel-by-pixel (laser or DMD mirror projection)
Energy Control	Broad spectrum; requires filtering	Narrow-band, energy-efficient, wavelength-tuned



Source: <https://zeiss-campus.magnet.fsu.edu/articles/lightsources/metalhalide.html>

Conventional Exposure tool:

- Peak = i-line (365nm)
- No possibility to adjust
- 365nm „cures“ top of resist
- „Closes“ top surface of resist
- Bottom not strongly polymerized



Multi-Wavelength DI-tool:

- Multiple peaks (e.g. 365/380/395/405 nm)
- Adjustable
- Find suitable parameter to „cure“ resist top to bottom
- Resist more homogenously polymerized
- Higher flexibility!

Developments of the light source

Schmoll
DI Gen. 1
1 Wavelength
Light source: **Diode laser**
Wavelength: **405nm**

Schmoll
DI Gen. 2
2 Wavelengths
Light source: **LED**
Wavelengths: **365 + 385nm**

Schmoll
DI Gen. 3
4 Wavelengths
Light source: **LED**
Wavelengths: **365 + 385 + 395 + 405nm**

Schmoll
Fineline
1 Wavelength
Light source: **Lasercomp.**
Wavelength: **h-line**

Market participant
A-Model
1 Wavelength
Light source: **Laser**
Wavelength: **355nm**

Market participant
B-Model
2 Wavelengths
Light source: **Laser**
Wavelengths: **375 + 405nm**

Market participant
C-Model
3 Wavelengths
Light source: **LED**
Wavelengths: **365 + 385 + 405nm**

Stepper
D-Model
1 Wavelength
Light source: **Deep-UV**
Wavelength: **i-line**

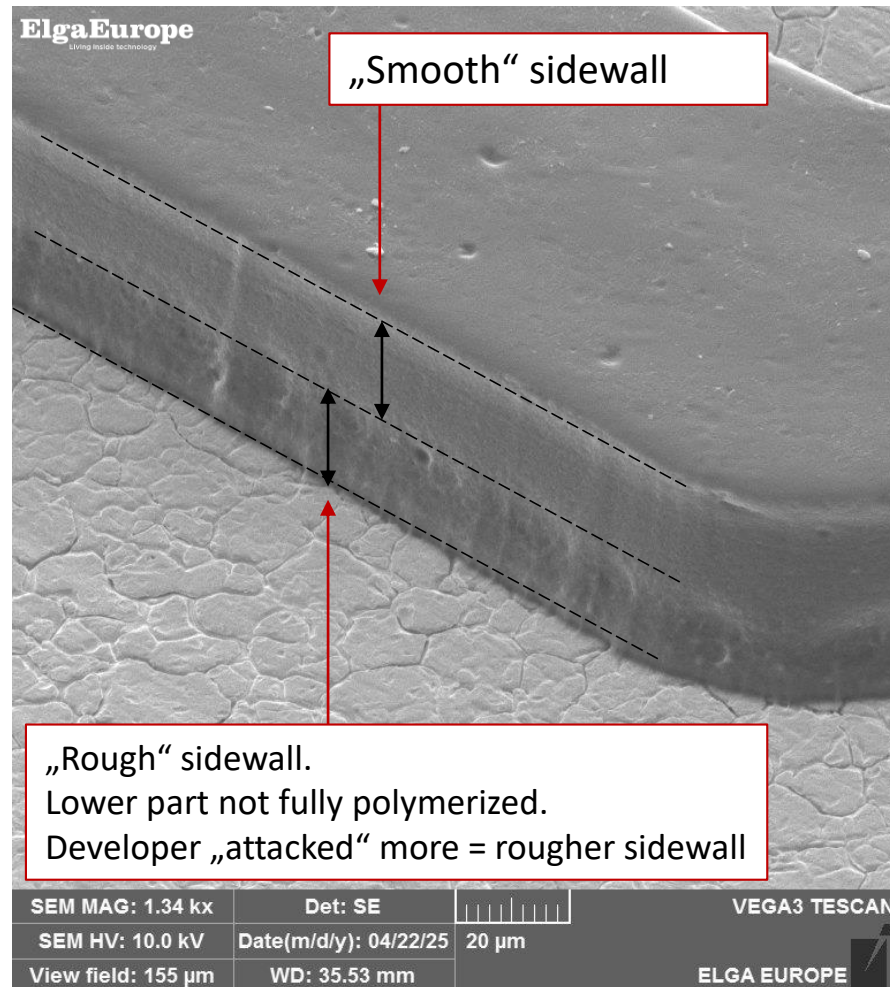
Developments of Materials (Resist)

Standard
Resist
(not specifically designed for
Wavelength-Peaks)

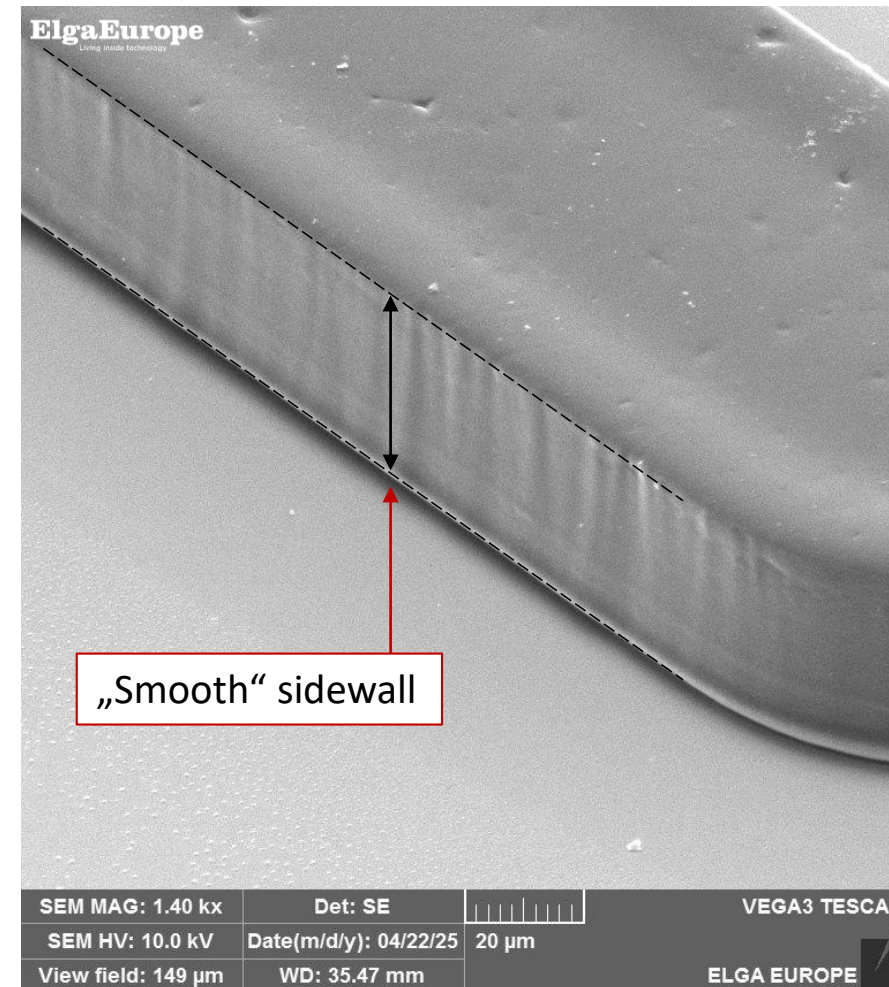
LDI
Resist
(355 – 365nm)

DI
Resist
(broad bandwidth:
365 – 405nm)

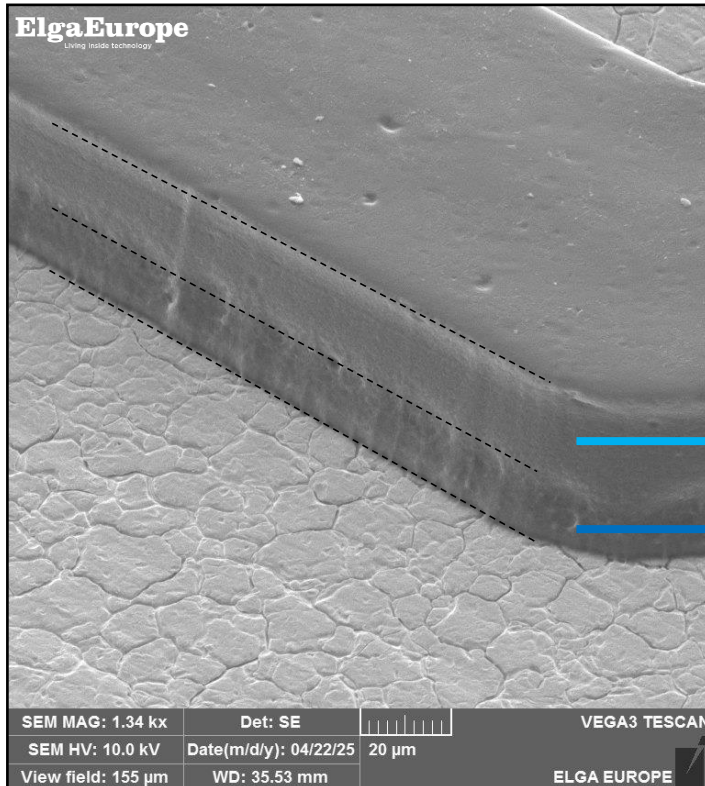
- 1) Existing Liquid films (mostly **i-line**),
high energy
- 2) High-Res Dryfilm Resists (mostly **h-line**),
lower energy



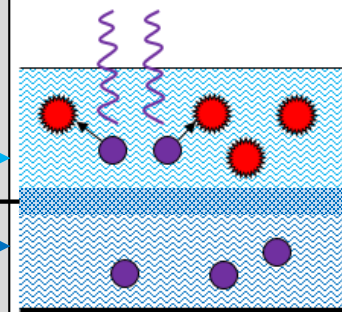
AF250E



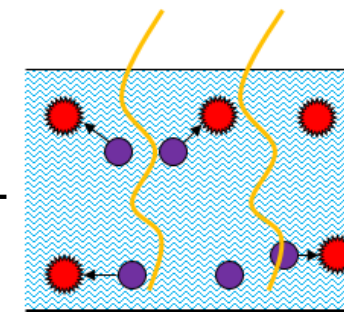
AM150 DI



Short wave UV

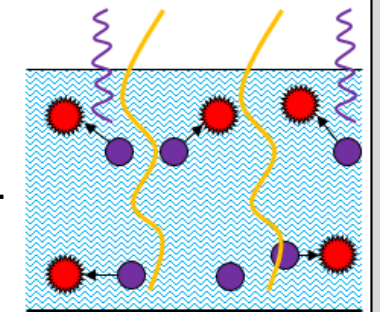


Long wave UV



Long wave UV

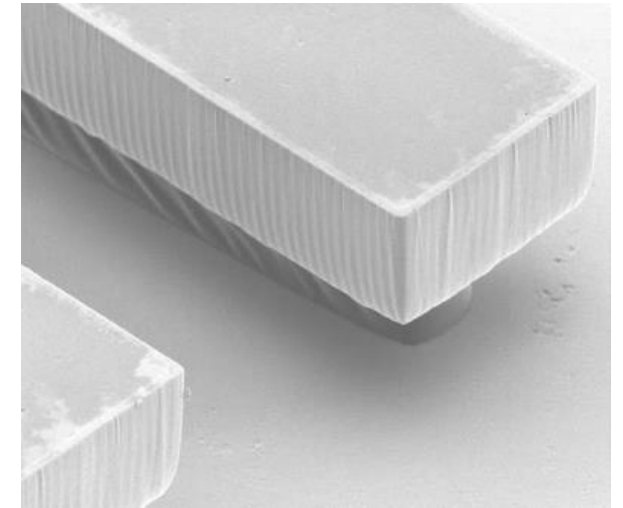
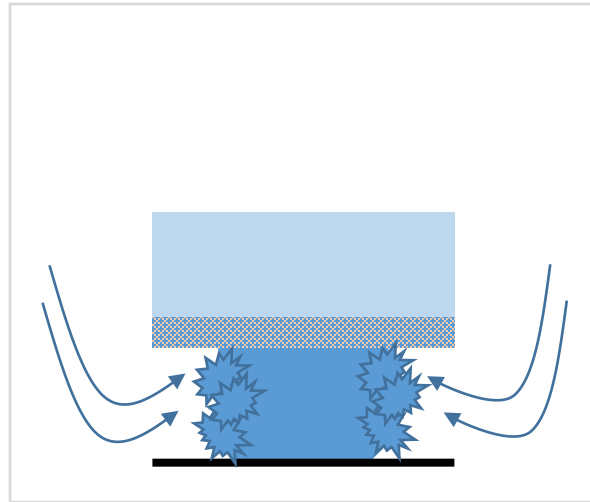
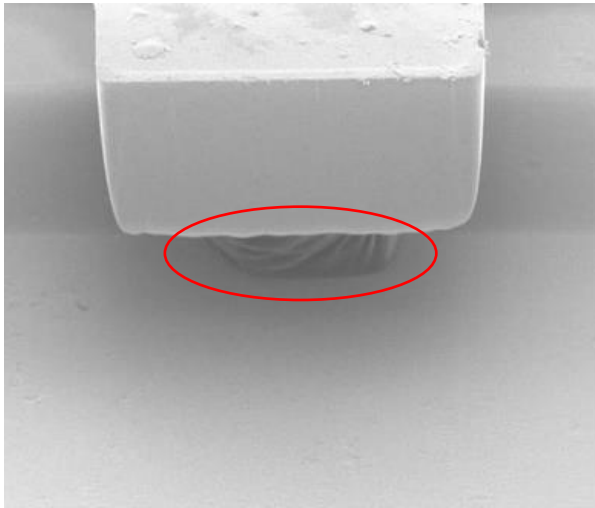
Short wave UV

 Photo initiator Excited photo initiator

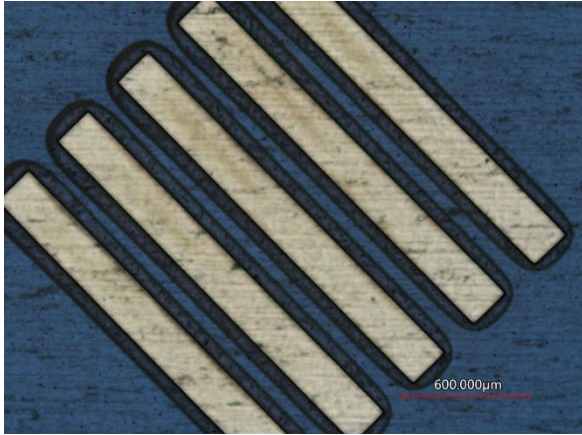
Short wave UV can't reach at bottom.
Excites the photo initiators **only near surface**.

Long wave UV **reaches at bottom**.
Photo initiators excited, but higher energy required = longer time

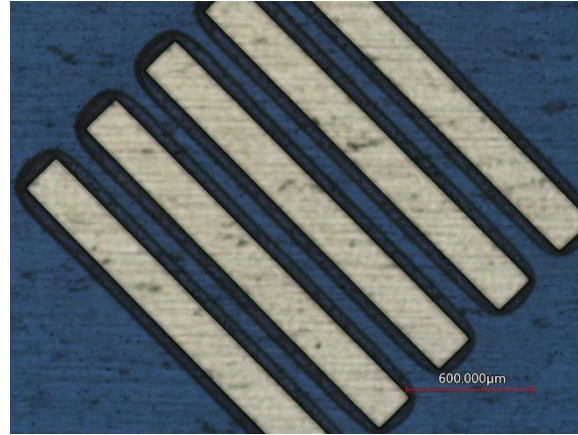
Short wave UV excites photo initiators near surface.
Long wave UV excites photo initiators at bottom.
Overall resist imaged more **homogeneously**.



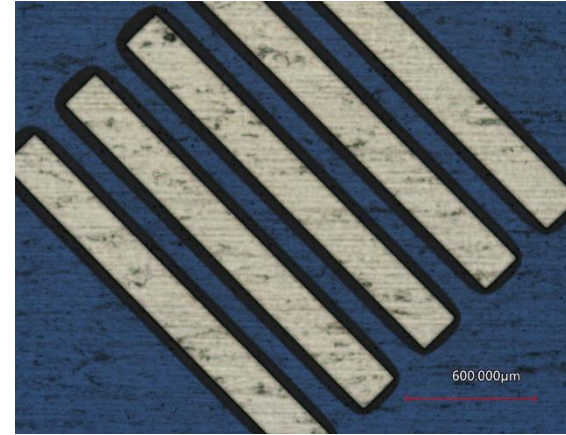
„Triple lamination“: Resist thickness total = 120 μm



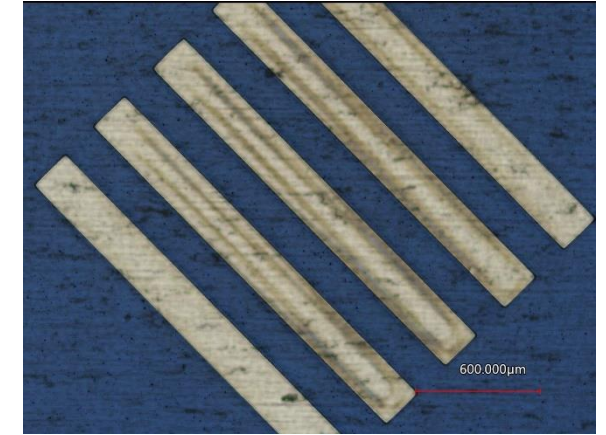
365nm



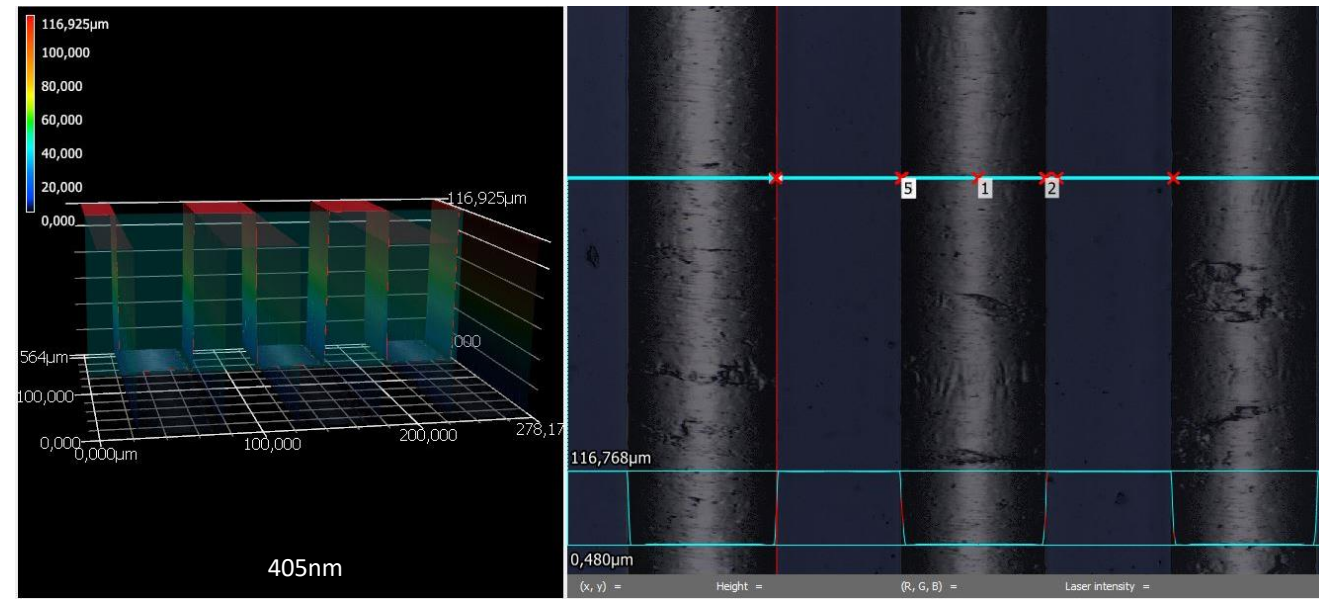
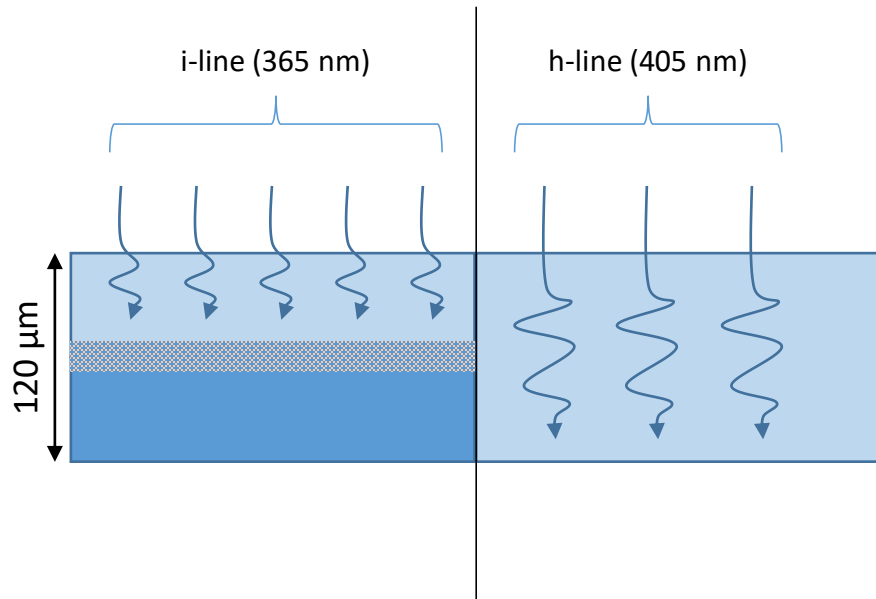
380nm

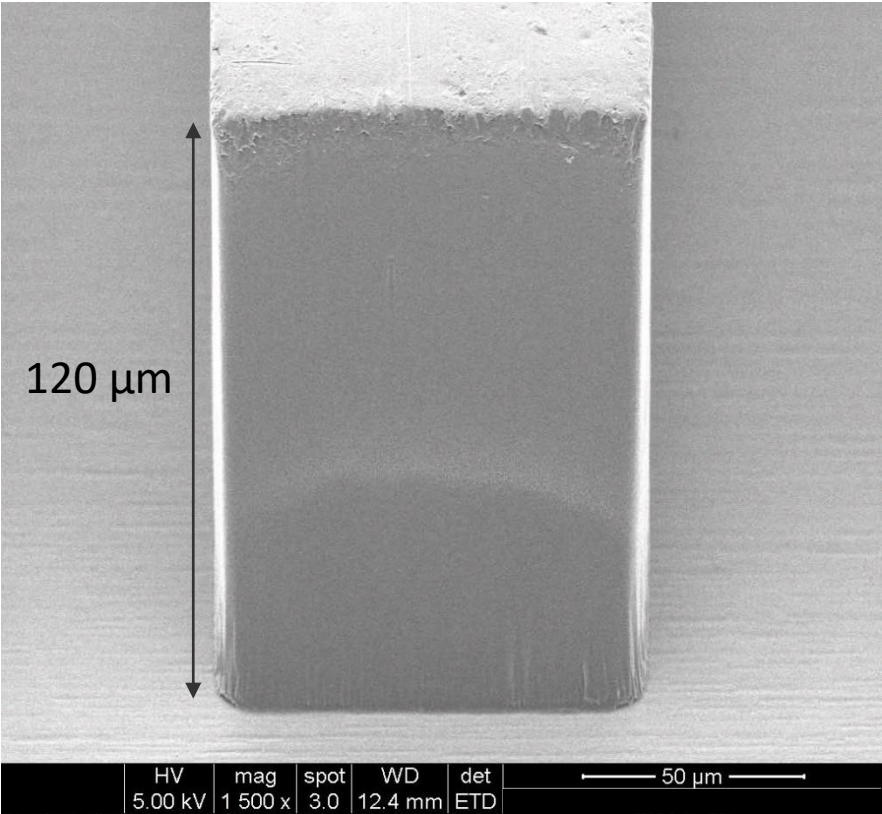
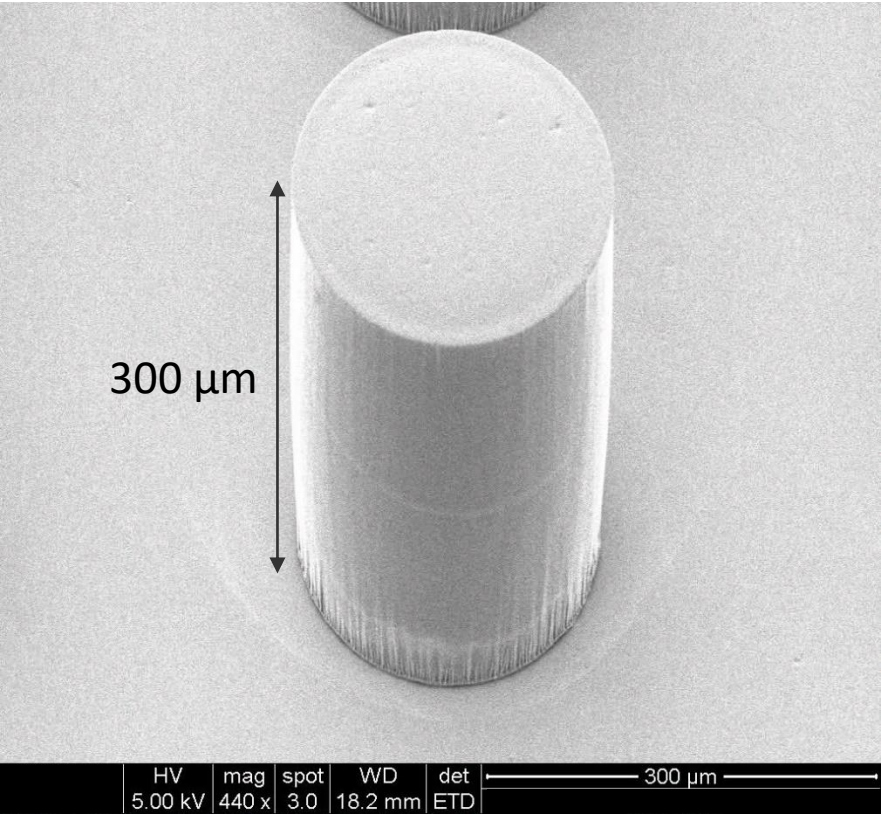
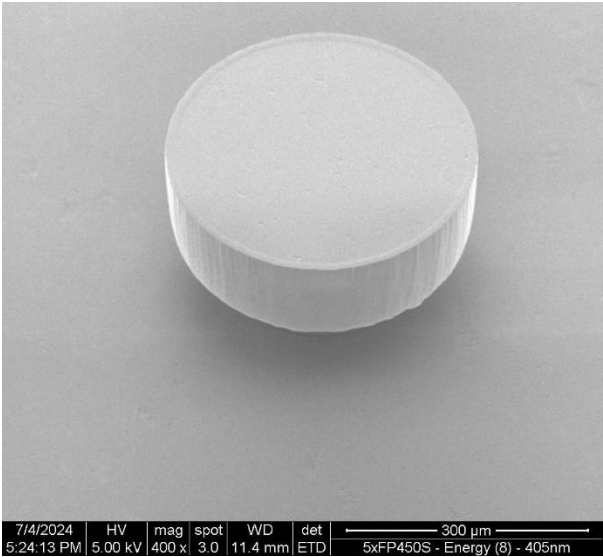


395nm

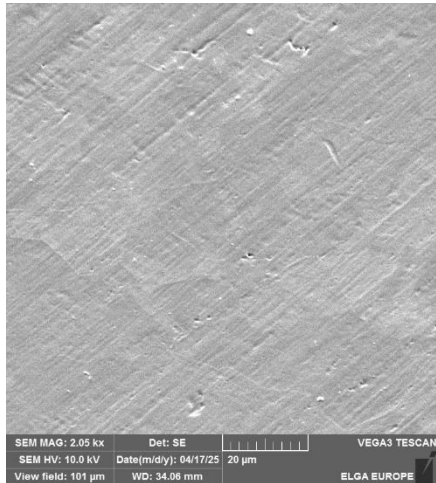


405nm

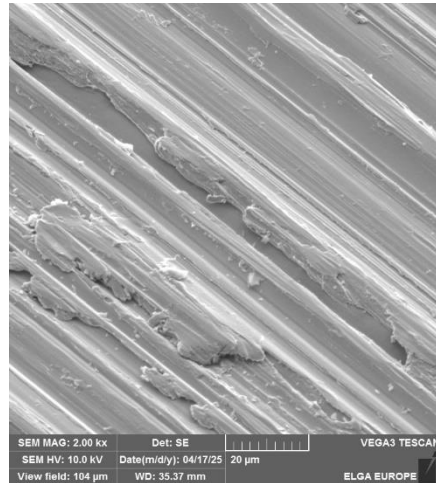




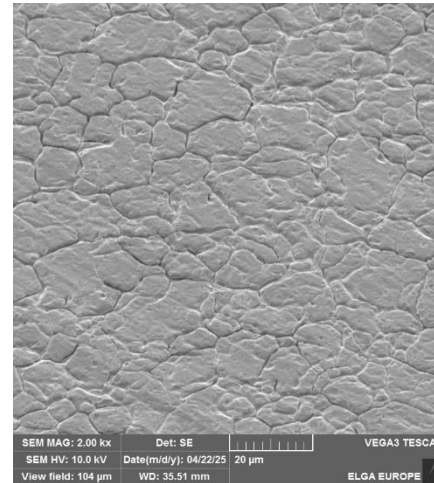
Tests and SEM Pictures in collaboration with **ElgaEurope**
Living inside technology



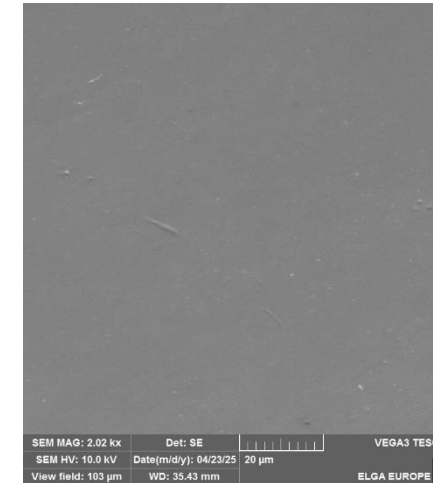
INOX BA MIRROR



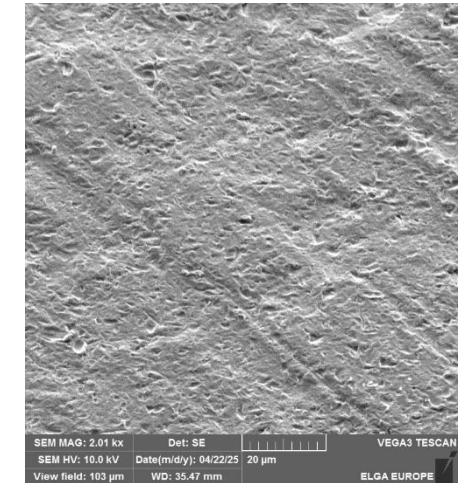
INOX SATIN



INOX 2B



INOX SUPERMIRROR



BRASS

Different Material & Surface treatment

+

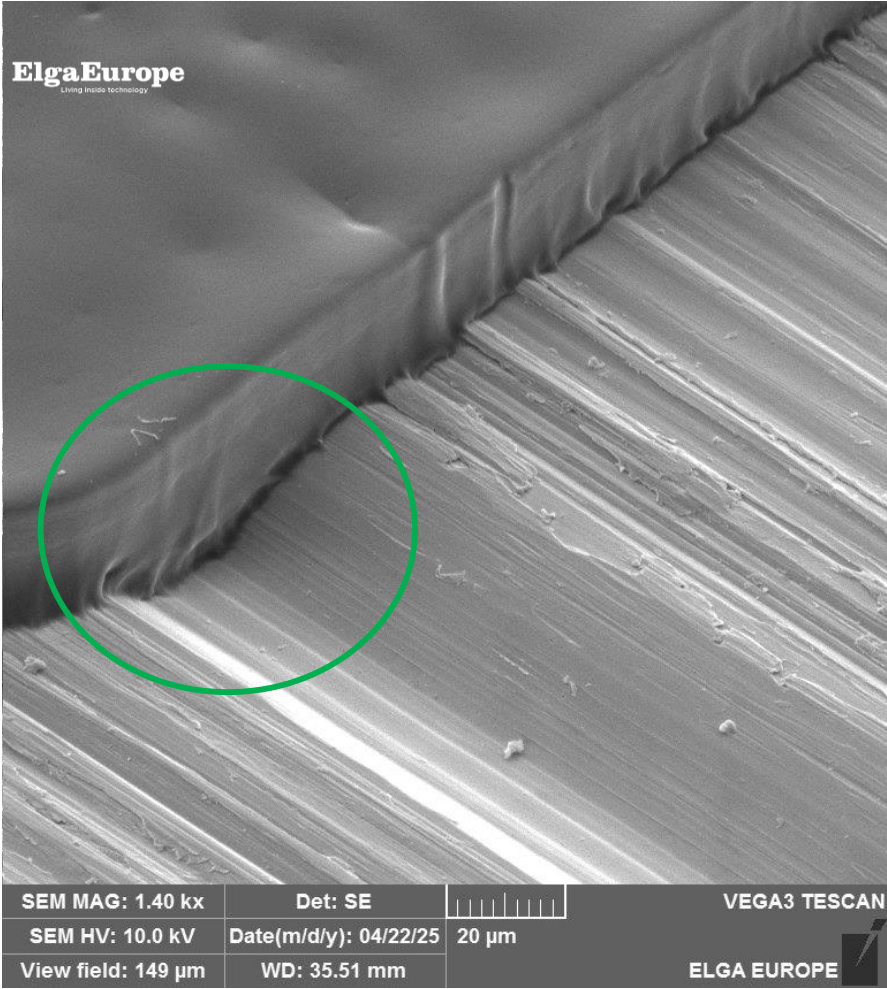
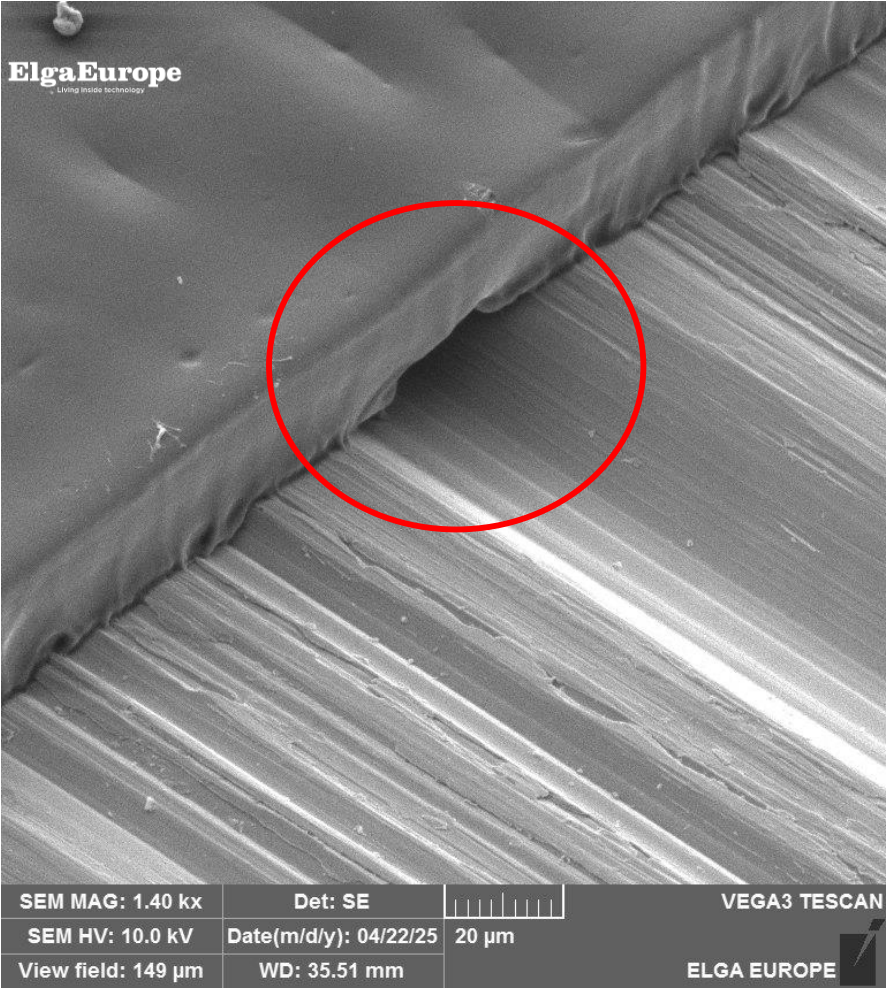
Same Photoresist

=

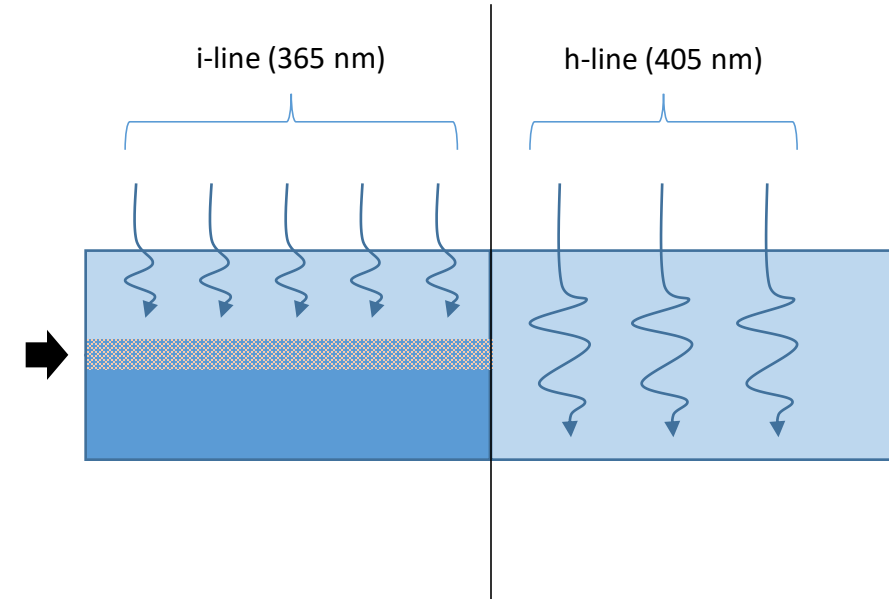
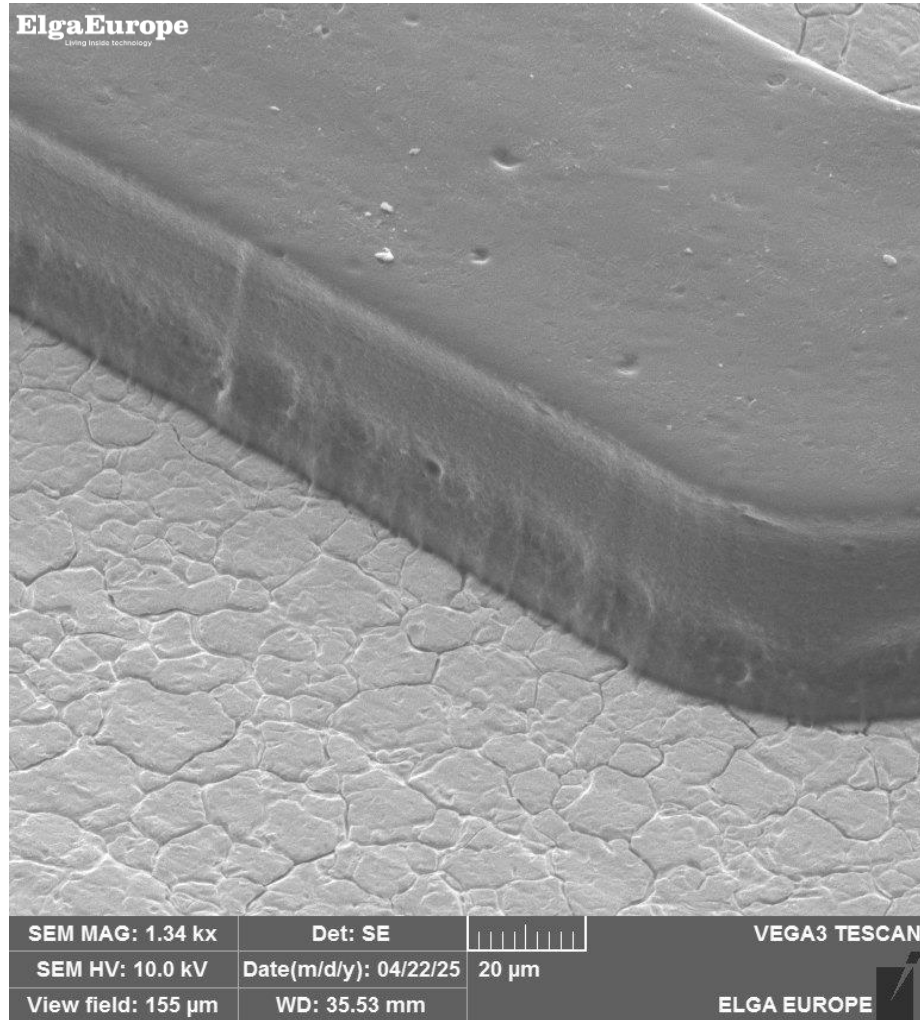
Different Recipe

Common Materials Used in Chemical Etching

Material	Properties
Stainless Steel	Corrosion-resistant, strong, chemically etchable with ferric chloride
Copper	Highly conductive, easily etched, used with cupric or ferric chloride
Brass (Copper-Zinc alloy)	Good machinability, decorative finish, etches similarly to copper
Nickel	Hard, corrosion-resistant, precise etching with nitric acid or ferric chloride
Aluminum	Lightweight, conductive, etched with nitric acid mixtures
Titanium	Very strong, corrosion-resistant, etched with aggressive etchants (HF-based)
Molybdenum	High-temperature stability, difficult to etch, used with specialized etchants
Phosphor Bronze	Good conductivity and wear resistance
Beryllium Copper	Excellent electrical properties and fatigue resistance
Inconel (Nickel Alloys)	Heat and oxidation resistant, used in harsh environments



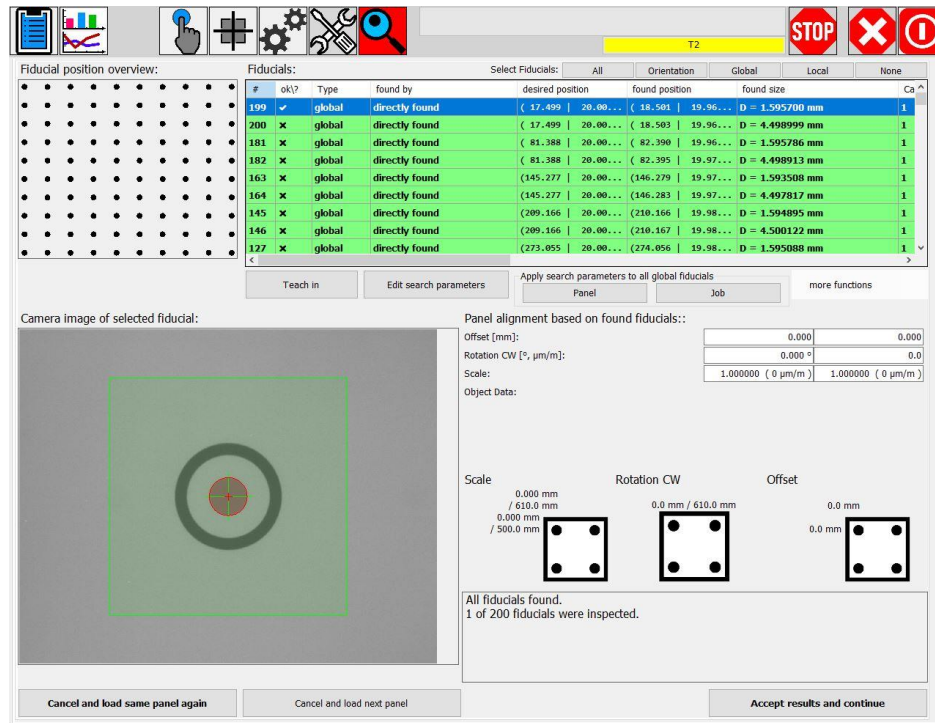
SUMMARY: EFFECT OF WAVELENGTHS



Resist surface „closes“ with lower wavelength;
„blocks“ higher wavelength from penetrating through
to the bottom for full polymerization.

Result: Bottom part „weaker“ against developer.
Leads to rougher sidewall
(and undercut)

At higher wavelength, the resist is imaged
more homogeneously across complete depth.
Fuller polymerization leading to smoother
sidewall, as developer „attacks“ equally.



Screenshot: Schmoll MDI User-Interface

Many different alloys, stainless steels, ...

- ... have very different surfaces
- ... have different reflection
- ... have different thermal characteristics
- ... behave differently during lamination (material „moves“ more than others)

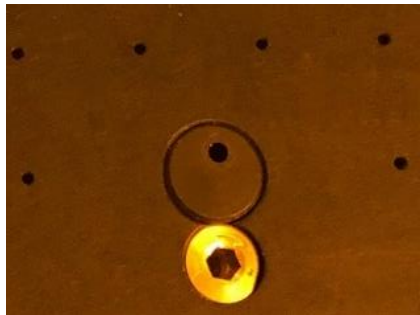
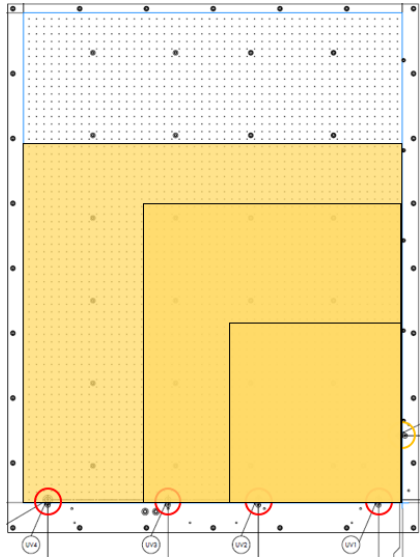
→ Image control
(through optimum recipe + accurate alignment)

→ Avoid different profile when etching one side more than the other



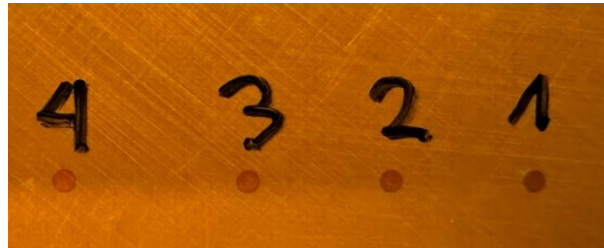
MDI

COLOR CHANGE ON RESIST FOR UV-MARKER



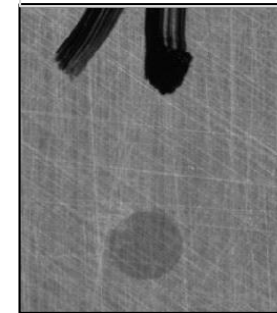
RESIST A

DuPont MM120i

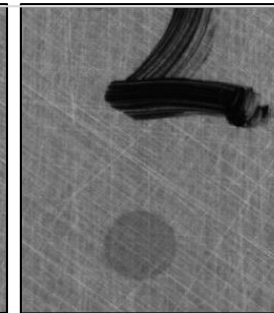


*Photo results with phone camera

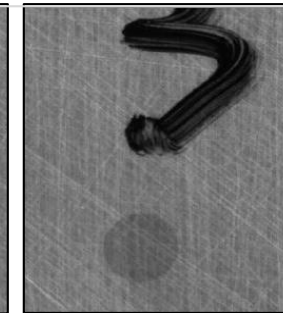
*Photo results with registration camera on machine



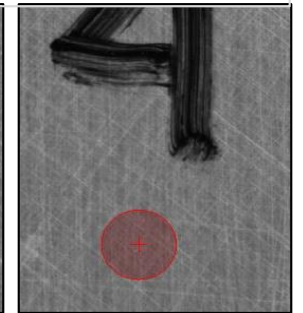
1 time exposure



2 times exposure



3 times exposure



4 times exposure

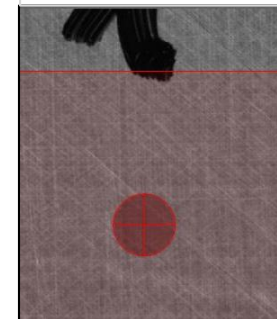
RESIST B

Eternal E9220

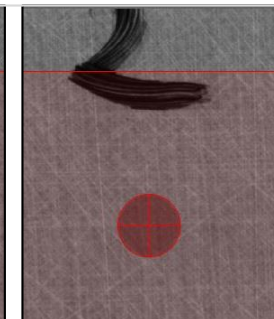


*Photo results with phone camera

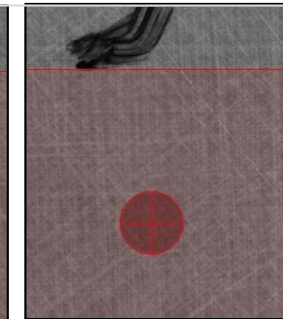
*Photo results with registration camera on machine



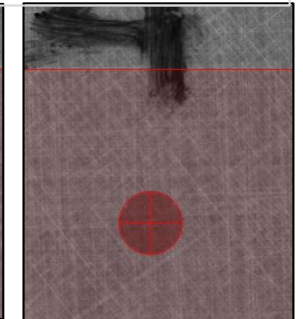
1 time exposure



2 times exposure



3 times exposure



4 times exposure

„All Resists can be
exposed with DI“

„Exchanging Exposure
machine does not require
change of resist type“

„Right exposure
for right material“

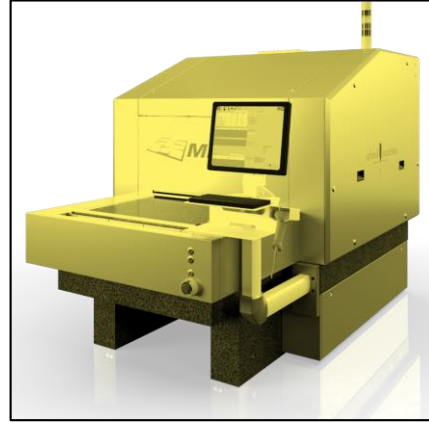
„Right Recipe for
right material!“



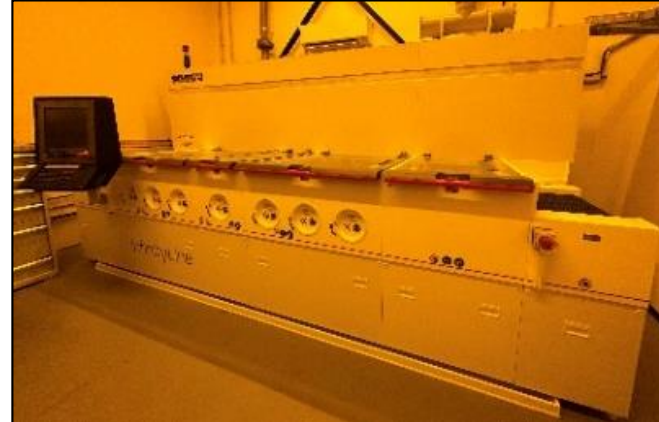
Correct choice of Direct Imaging technology
can provide a real solution!



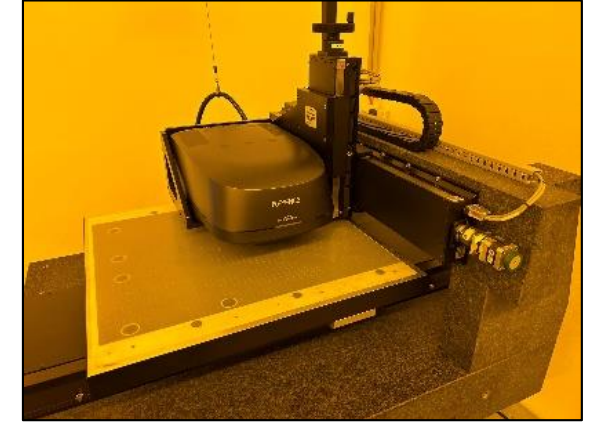
Spin Coater & Developer



MDI Imager



Developer (Photoresist)



Laser Microscope stage

- Demo Machine (available with different Photohead resolutions)
- Developer
- Laser Microscope (stage)
- Spin coater for liquid resist
- Developer for liquid resist
- Hot plate
- Equipment to prepare Cross-Sections
- Diverse Resist materials (different thicknesses; standard and **high resolution**)

Convince yourself – make a test

THANK YOU



